Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	73527	semiconductor and cmos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:53
L2	36842	1 and gate and source and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:53
L3	1518	2 and ferroelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:54
L4	1187	3 and channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:54
L5	696	4 and (gate adj (insulat\$3 or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:55

Freeform Search

	US Pre-Grant Publication Full-Text Database US Patents Full-Text Database US OCR Full-Text Database EPO Abstracts Database JPO Abstracts Database Derwent World Patents Index IBM Technical Disclosure Bulletins
Term:	semiconductor and cmos and ferroelectric
	Documents in Display Format: FULL Starting with Number 1 O Hit List O Hit Count O Side by Side O Image Search Clear Interrupt
	Search History
•	y, March 29, 2005 Printable Copy Create Case
DATE: Tuesda	

END OF SEARCH HISTORY